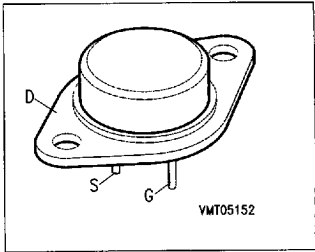


SIPMOS® Power Transistor

BUZ 64

- N channel
- Enhancement mode
- Avalanche-rated



Type	V_{DS}	I_D	$R_{DS(on)}$	Package ¹⁾	Ordering Code
BUZ 64	400 V	11.5 A	0.4 Ω	TO-204 AA	C67078-S1017-A2

Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current, $T_C = 31\text{ }^{\circ}\text{C}$	I_D	11.5	A
Pulsed drain current, $T_C = 25\text{ }^{\circ}\text{C}$	$I_{D\text{ puls}}$	46	
Avalanche current, limited by $T_{J\text{ max}}$	I_{AR}	11.5	
Avalanche energy, periodic limited by $T_{J(max)}$	E_{AR}	13	mJ
Avalanche energy, single pulse $I_D = 11.5\text{ A}$, $V_{DD} = 50\text{ V}$, $R_{GS} = 25\text{ }\Omega$ $L = 8.87\text{ mH}$, $T_J = 25\text{ }^{\circ}\text{C}$	E_{AS}	670	
Gate-source voltage	V_{GS}	± 20	V
Power dissipation, $T_C = 25\text{ }^{\circ}\text{C}$	P_{tot}	125	W
Operating and storage temperature range	T_J, T_{stg}	- 55 ... + 150	$^{\circ}\text{C}$
Thermal resistance, chip-case	R_{thJC}	≤ 1.0	K/W
DIN humidity category, DIN 40 040		C	-
IEC climatic category, DIN IEC 68-1		55/150/56	

1) See chapter Package Outlines.

Electrical Characteristicsat $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static characteristics

Drain-source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$	$V_{(BR)DS}$	400	—	—	V
Gate threshold voltage $V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$	$V_{GS(th)}$	2.1	3.0	4.0	
Zero gate voltage drain current $V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$ $T_j = 25\text{ }^{\circ}\text{C}$ $T_j = 125\text{ }^{\circ}\text{C}$	I_{DSS}	— —	0.1 10	1.0 100	μA
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	—	10	100	nA
Drain-source on-resistance $V_{GS} = 10\text{ V}$, $I_D = 7.5\text{ A}$	$R_{DS(on)}$	—	0.35	0.40	Ω

Dynamic characteristics

Forward transconductance $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$, $I_D = 7.5\text{ A}$	g_{fs}	5.0	9.5	—	S
Input capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	—	1900	2500	pF
Output capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	—	260	400	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	—	110	170	
Turn-on time t_{on} , ($t_{on} = t_{d(on)} + t_r$) $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $R_{GS} = 50\text{ }\Omega$	$t_{d(on)}$	—	30	45	ns
	t_r	—	90	135	
Turn-off time t_{off} , ($t_{off} = t_{d(off)} + t_f$) $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $R_{GS} = 50\text{ }\Omega$	$t_{d(off)}$	—	350	465	
	t_f	—	100	135	

Electrical Characteristics (cont'd)
at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

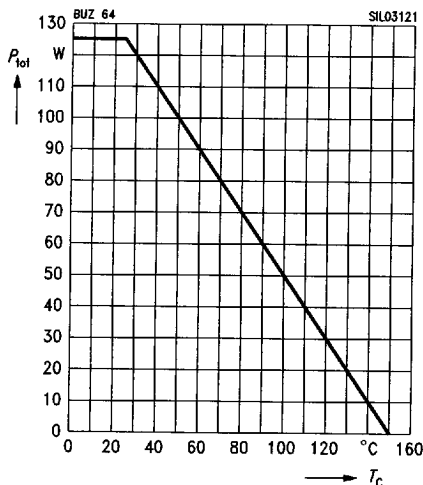
Reverse diode

Continuous reverse drain current $T_C = 25\text{ }^{\circ}\text{C}$	I_S	—	—	11.5	A
Pulsed reverse drain current $T_C = 25\text{ }^{\circ}\text{C}$	I_{SM}	—	—	46	
Diode forward on-voltage $I_S = 23\text{ A}$, $V_{GS} = 0\text{ V}$	V_{SD}	—	1.1	1.4	V
Reverse recovery time $V_R = 30\text{ V}$, $I_F = I_S$, $di_F / dt = 100\text{ A}/\mu\text{s}$	t_{rr}	—	180	—	ns
Reverse recovery charge $V_R = 30\text{ V}$, $I_F = I_S$, $di_F / dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	—	1.2	—	μC

Characteristics at $T_j = 25^\circ\text{C}$, unless otherwise specified.

Total power dissipation

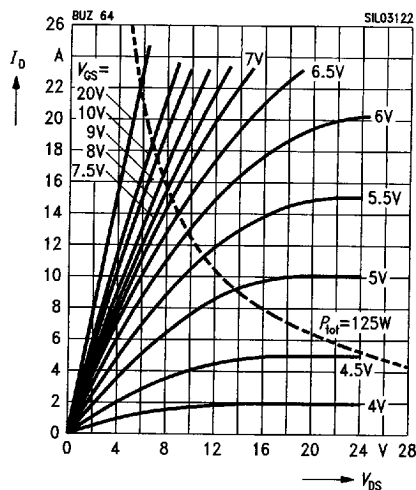
$$P_{\text{tot}} = f(T_C)$$



Typ. output characteristics

$$I_D = f(V_{\text{DS}})$$

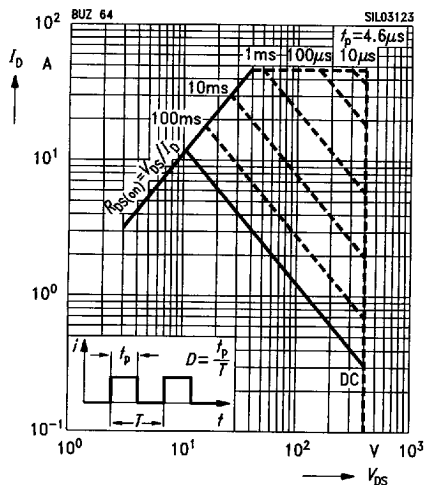
parameter: $t_p = 80 \mu\text{s}$



Safe operating area

$$I_D = f(V_{\text{DS}})$$

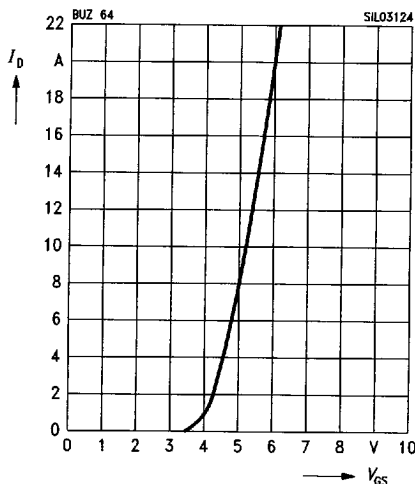
parameter: $D = 0.01$, $T_C = 25^\circ\text{C}$



Typ. transfer characteristics

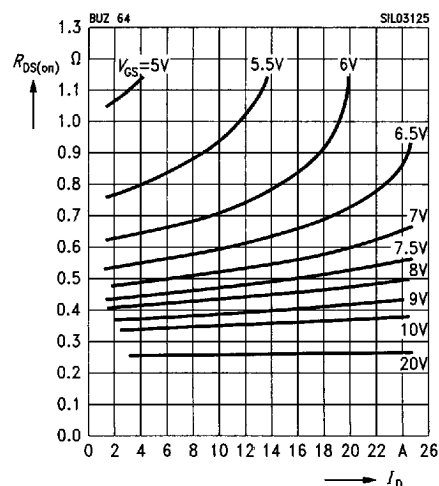
$$I_D = f(V_{\text{GS}})$$

parameter: $t_p = 80 \mu\text{s}$, $V_{\text{DS}} = 25\text{V}$

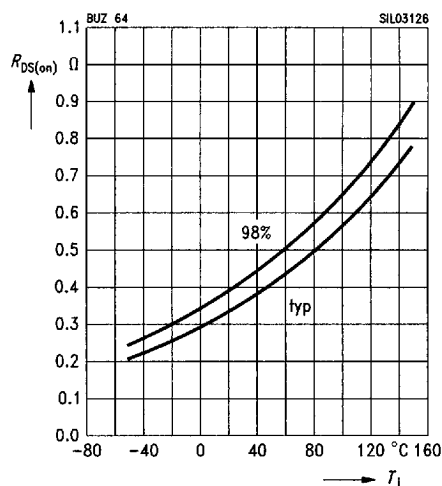


Typ. drain-source on-resistance

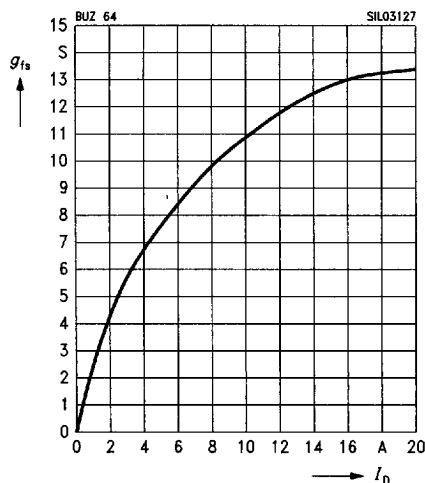
$$R_{DS(on)} = f(I_D)$$

parameter: V_{GS} **Drain-source on-resistance**

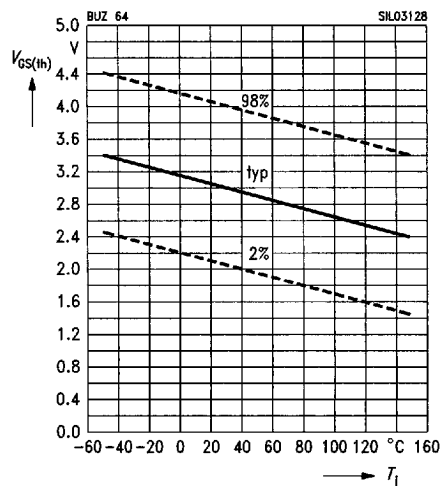
$$R_{DS(on)} = f(T_j)$$

parameter: $I_D = 7.5$ A, $V_{GS} = 10$ V, (spread)**Typ. forward transconductance**

$$g_{fs} = f(I_D)$$

parameter: $t_p = 80$ μs **Gate threshold voltage**

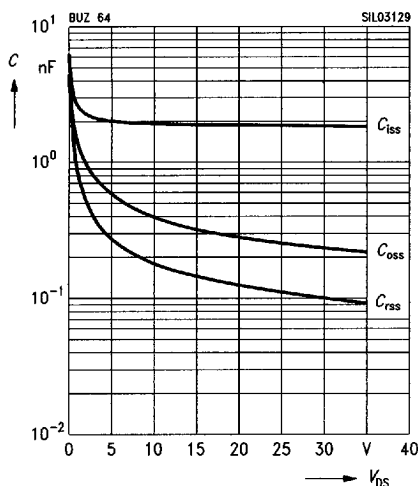
$$V_{GS(th)} = f(T_j)$$

parameter: $V_{GS} = V_{DS}$, $I_D = 1$ mA, (spread)

Typ. capacitances

$$C = f(V_{DS})$$

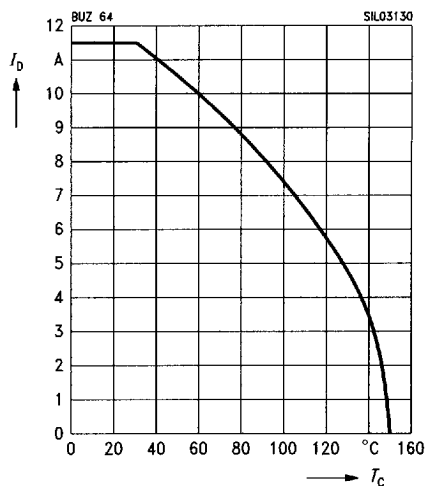
parameter: $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$



Drain current

$$I_D = f(T_C)$$

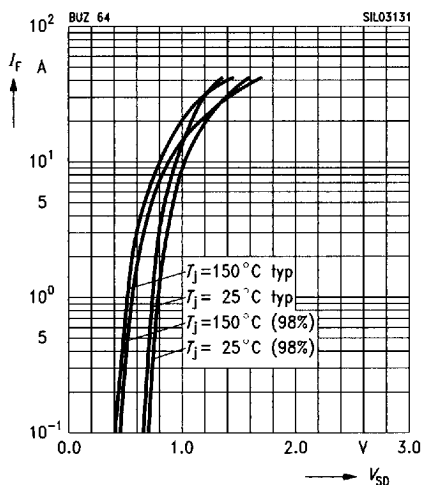
parameter: $V_{GS} \geq 10 \text{ V}$



Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

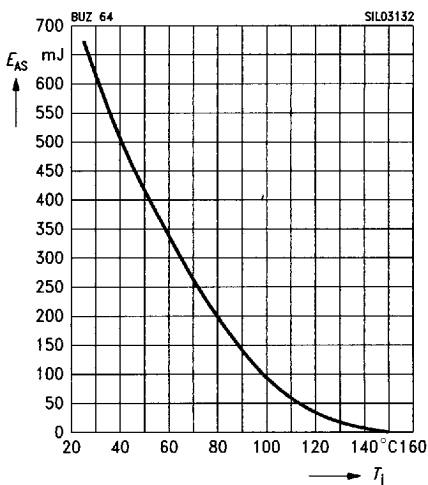
parameter: T_j , $t_p = 80 \mu\text{s}$, (spread)



Avalanche energy $E_{AS} = f(T_j)$

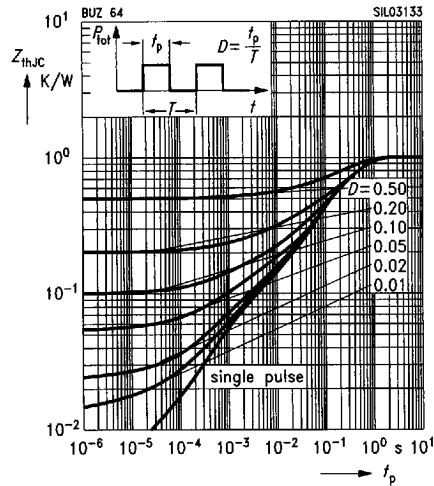
parameter: $I_D = 11.5 \text{ A}$, $V_{DD} = 50 \text{ V}$

$R_{GS} = 25 \Omega$, $L = 8.87 \text{ mH}$



Transient thermal Impedance

$Z_{thJC} = f(t_p)$
parameter: $D = t_p / T$



Typ. gate charge

$V_{GS} = f(Q_{Gate})$
parameter: $I_{D\ puls} = 21\ A$

